SK20GH123



IGBT Module

SK20GH123

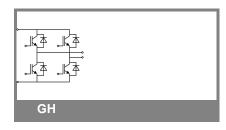
Preliminary Data

Features

- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N-channel homogeneous silicon structure (NPT-Non punch-through IGBT)
- · High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63532

Typical Applications*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



Absolute Maximum Ratings $T_s = 25 ^{\circ}\text{C}$, unless otherwise specified					
Symbol	Conditions		1	Values	Units
IGBT	•				•
V_{CES}	T _j = 25 °C			1200	V
I _C	T _j = 125 °C	T _s = 25 °C		23	Α
		$T_s = 80 ^{\circ}C$		15	Α
I _{CRM}	I _{CRM} = 2 x I _{Cnom}			30	Α
V_{GES}				± 20	V
t _{psc}	V_{CC} = 600 V; $V_{GE} \le 20$ V; $V_{CES} < 1200$ V	T _j = 125 °C		10	μs
Inverse D	Diode				
I _F	T _j = 150 °C	$T_s = 25 ^{\circ}C$		24	Α
		T_s = 80 °C		17	Α
I _{FRM}	I _{FRM} = 2 x I _{Fnom}				Α
I _{FSM}	t _p = 10 ms; half sine wave	T _j = 150 °C		180	Α
Module					
$I_{t(RMS)}$					Α
T _{vj}				-40 + 150	°C
T _{stg}				-40 + 125	°C
V _{isol}	AC, 1 min.			2500	V

Characteristics $T_s =$			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0.6$ mA		4,5	5,5	6,5	V	
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = V_{CES}$	T _j = 25 °C			0,1	mA	
		T _j = 125 °C				mA	
I _{GES}	V _{CE} = 0 V, V _{GE} = 30 V	T _j = 25 °C			480	nA	
		T _j = 125 °C				nA	
V _{CE0}		T _j = 25 °C		1,2		V	
		T _j = 125 °C		1,2		V	
r _{CE}	V _{GE} = 15 V	T _j = 25°C		86		mΩ	
		T _j = 125°C		126		mΩ	
V _{CE(sat)}	I _{Cnom} = 15 A, V _{GE} = 15 V		2	2,5	3	V	
		$T_j = 125^{\circ}C_{chiplev.}$		3,1	3,7	V	
C _{ies}				1		nF	
C _{oes}	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,15		nF	
C _{res}				0,07		nF	
Q_G	V _{GE} =0 20 V			90		nC	
t _{d(on)}				35		ns	
lt,	$R_{Gon} = 40 \Omega$	V _{CC} = 600V		45		ns	
Ė _{on}	D 40.0	I _C = 15A		2		mJ	
^L d(off)	R_{Goff} = 40 Ω	T _j = 125 °C		250		ns	
t _f ⊏		V _{GE} =±15V		70 1.8		ns m.l	
E _{off}				1,8		mJ	
$R_{th(j-s)}$	per IGBT				1,4	K/W	

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SEMITOP® 2

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Characteristics							
Symbol	Conditions		min.	typ.	max.	Units	
Inverse Diode							
$V_F = V_{EC}$	$I_{Fnom} = 15 \text{ A}; V_{GE} = 0 \text{ V}$	T _j = 25 °C _{chiplev.}		2	2,5	V	
		$T_j = 125 ^{\circ}C_{chiplev.}$		1,8	2,3	V	
V_{F0}		T _j = 125 °C		1	1,2	V	
r _F		T _j = 125 °C		53	73	mΩ	
I _{RRM}	I _F = 15 A	T _i = 125 °C		16		Α	
Q_{rr}	di/dt = -200 A/µs	,		2,7		μC	
E _{rr}	V _{CC} = 600V			0,6		mJ	
R _{th(j-s)D}	per diode				1,7	K/W	
M _s	to heat sink M1				2	Nm	
w				21		g	

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

